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Overview

Diagrams

Electrical Rating	Symbol	Min	Typ	Max	Unit
Collector to Emitter Saturation Voltage	$V_{CE(sat)}$			1.00	V
DC Current Gain	HFE	20.00		100.00	

Maximum Electrical Rating	Symbol	Min	Typ	Max	Unit
Breakdown Voltage, Collector-Base (Emitter Open)	$V_{BR(CBO)}$			80.00	V
Collector Current (dc)	$I_C$			15.00	A
Collector-Emitter Voltage (Base Open)	$V_{CEO}$			80.00	V
Emitter-Base Voltage (Collector Open)	$V_{EBO}$			6.00	V
Power Dissipation, Total	$P_T$			160.00	W

This part can be found in the following product categories:

- ▶ Discretes ▶ Transistors ▶ BJT( BiPolar Junction Transistor) ▶ **FNP** Transistor
- ▶ Non-Radiation Hardened Devices ▶ Transistors ▶ BJT( BiPolar Junction Transistor) ▶ **NPN** Transistor

Related Links

- Technical support
- Sales Contacts**
- Available Stock
- Sales Contacts
- RFQ/Samples